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Vishay/Siliconix SQ7002K-T1-GE3

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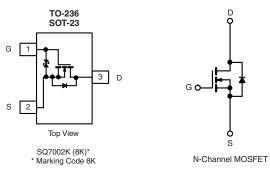


# SQ7002K

**Vishay Siliconix** 

### Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	60
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = 10 V	1.30
$R_{DS(on)}\left(\Omega\right)$ at $V_{GS}$ = 4.5 V	1.90
I <sub>D</sub> (A)	0.32
Configuration	Single



#### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- AEC-Q101 Qualified<sup>d</sup>
- ESD Protection 2000 V
- Compliant to RoHS Directive 2002/95/EC



ORDERING INFORMATION	
ORDERING INFORMATION	

Package	SOT-23	
Lead (Pb)-free and Halogen-free	SQ7002K-T1-GE3	

ABSOLUTE MAXIMUM RATIN	<b>GS</b> (T <sub>C</sub> = 25 °C, unle	ess otherwise not	ed)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage Gate-Source Voltage		V <sub>DS</sub>	60	V
		V <sub>GS</sub>	± 20	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	0.32	
	T <sub>C</sub> = 125 °C		0.24	
Continuous Source Current (Diode Conduction	on) <sup>a</sup>	I <sub>S</sub>	0.32	A
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	0.8	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	0.5	W
	T <sub>C</sub> = 125 °C		0.17	vv
Operating Junction and Storage Temperature	Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	350	°C/W	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	300	0/10	

Notes

a. Package limited.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static		1		li	1	I		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	60	-	-		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0	1.8	2.5	V	
Coto Course Leskage	1	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 50		
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V			± 1	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
-		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	0.5	-	-	А	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 0.5 A	-	1.07	1.30	Ω	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 0.5 A, T <sub>J</sub> = 125 °C	-	-	2.33		
	$V_{GS} = 1$	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 0.5 A, T <sub>J</sub> = 175 °C	-	-	2.97		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 0.2 A	-	1.42	1.90		
Forward Transconductanceb	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.2 \text{ A}$		-	100	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 30 V, f = 1 MHz	-	19	24	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	4.8	6		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	2.3	3		
Total Gate Charge <sup>c</sup>	Qg			-	0.9	1.4		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 4.5 V	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 0.25 \text{ A}$	-	0.3	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	0.4	-		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 30 \text{ V}, \text{ R}_L = 150 \ \Omega$ $\text{I}_D \cong 0.250 \text{ A}, \text{ V}_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_g = 120 \ \Omega$		-	14.6	22		
Rise Time <sup>c</sup>	tr			-	15.3	23	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	8.6	13		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	10.6	16		
Source-Drain Diode Ratings and Chara	acteristics (T <sub>C</sub> =	25 °C) <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	0.8	А	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	-	0.83	1.2	V		

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2$  %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



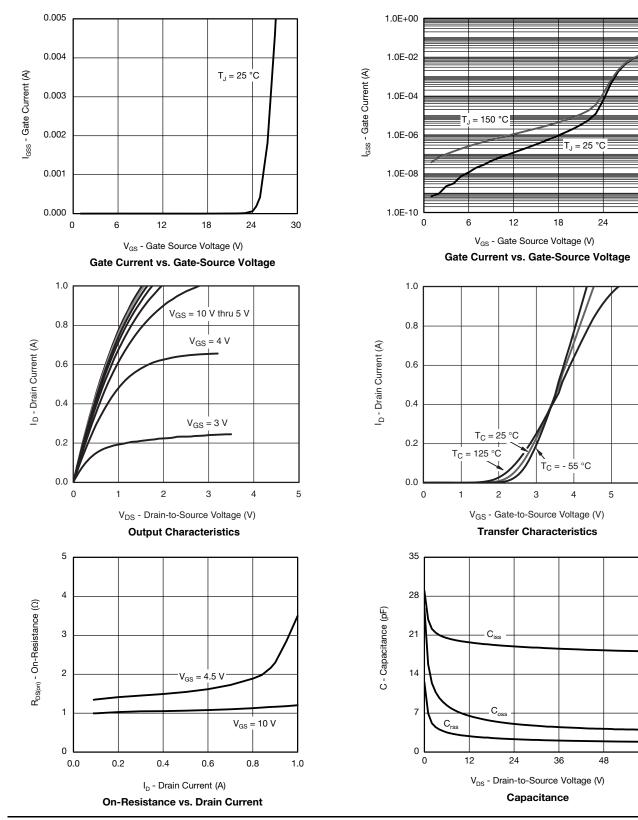


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30

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TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

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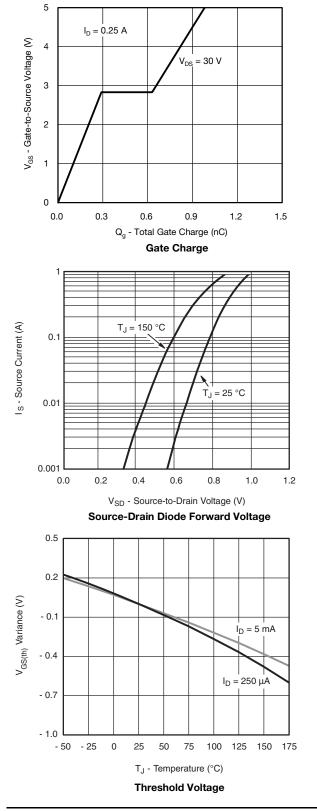


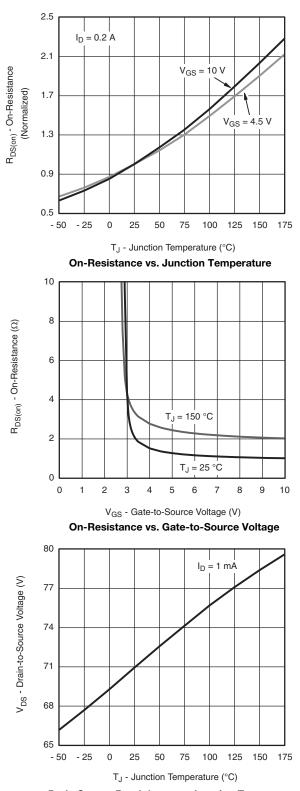
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#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)







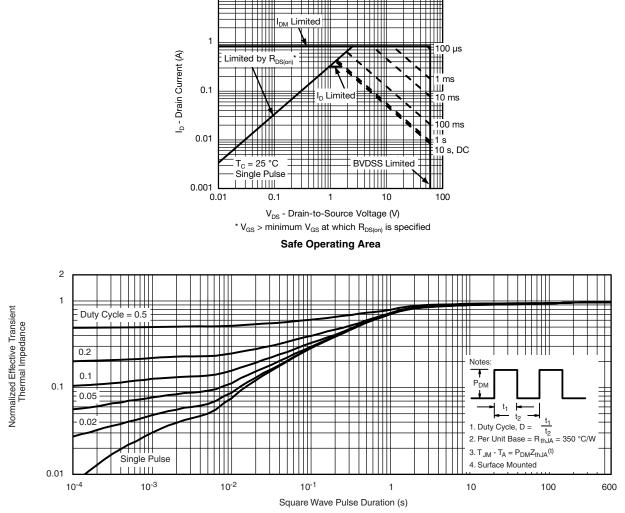


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#### **THERMAL RATINGS** ( $T_A = 25 \ ^{\circ}C$ , unless otherwise noted)

10



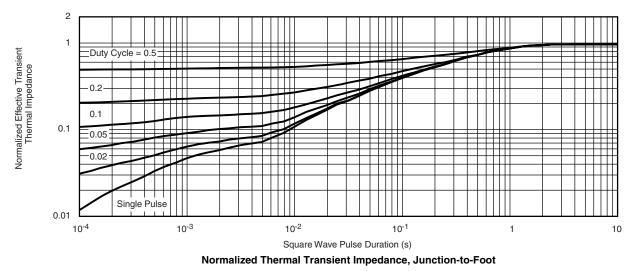
Normalized Thermal Transient Impedance, Junction-to-Ambient



## SQ7002K

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#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?65547">www.vishay.com/ppg?65547</a>.





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